

ABSTRACT

An apparatus for electropolishing a conductive layer on a wafer using a solution is disclosed. The apparatus comprises an electrode assembly immersed in the solution configured proximate to the conductive layer having a longitudinal dimension extending to at least a periphery of the wafer, the electrode assembly including an elongated contact electrode configured to receive a potential difference, an isolator adjacent the elongated contact electrode, and an elongated process electrode adjacent the isolator configured to receive the potential difference, a voltage supply is configured to supply the potential difference between the contact electrode and the process electrode to electropolish the conductive layer on the wafer.